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DIGITAL TV TUNER IC

Check for Samples: SN761644

FEATURES

- Integrated Mixer/Oscillator/PLL and IF GCA
- Mirror Pin Package of SN761640
- VHF-L, VHF-H, UHF 3-Band Local Oscillator
- RF AGC Detector Circuit
- I²C Bus Protocol Bidirectional Data Transmission
- High-Voltage Tuning Voltage Output
- Four NPN-Type Band Switch Drivers
- One Auxiliary Port/5-Level ADC
- Crystal Oscillator Output
- Programmable Reference Divider Ratio (24/28/32/64/80/128)
- IF GCA Enable/Disable Control
- Selectable digital IFOUT and Analog IFOUT
- Standby Mode
- 5-V Power Supply
- 44-Pin Thin Shrink Small-Outline Package (TSSOP)

APPLICATIONS

- Digital TVs
- Digital CATVs
- Set-Top Boxes

(TOP VIEW) BS4 [44 T VLO OSCB 1 () UHF RF IN1 □ 2 43 T VLO OSC C UHF RF IN2 **□** 3 42 T VHI OSC B 41 T VHI OSC C VHI RF IN **∏** 4 VLO RF IN □ 5 40 UHF OSC B1 RF GND ☐ 6 39 UHF OSC C1 MIX OUT2 [38 T UHF OSC C2 37 UHF OSC B2 MIX OUT1 **∏** 8 IF IN □ 36 OSC GND RF AGC OUT [10 35 CP RF AGC BUF □ 34 **1** VTU 11 33 TIF GND BS3 [12 BS2 [13 32 AIF OUT BS1 [31 DIF OUT1 14 30 | DIF OUT2 SDA [15 SCL [16 29 T IF GCA CTRL 28 7 VCC AS [17 BUS GND [27 | IF GCA IN1 18 P5/ADC **1** 19 26 T IF GCA IN2 XTAL OUT 25 IF GCA GND 20 24 I IF GCA OUT2 XTAL2 [] 21 23 T IF GCA OUT1 XTAL1 ∏ 22

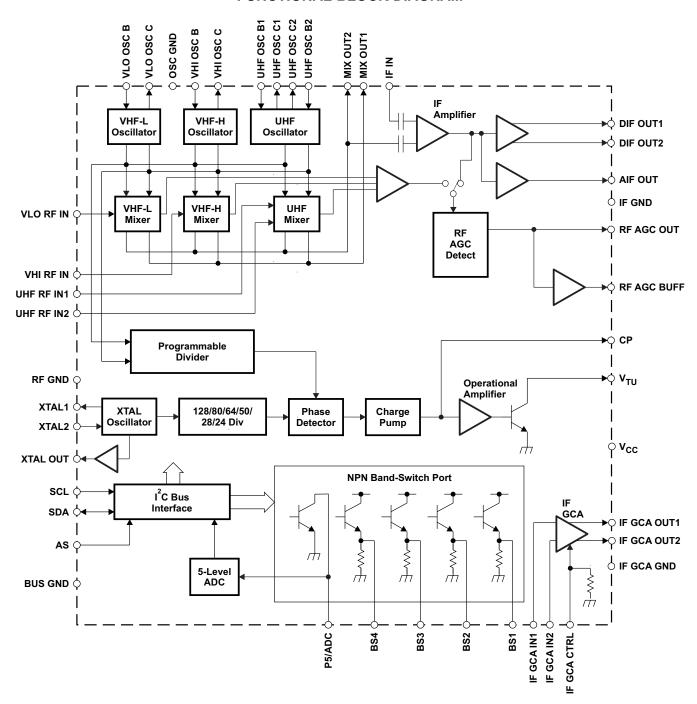
DBT PACKAGE

DESCRIPTION

The SN761644 is a low-phase-noise synthesized tuner IC designed for digital TV tuning systems. The circuit consists of a PLL synthesizer, three-band local oscillator and mixer, RF AGC detector circuit, and IF gain-controlled amplifier. The SN761644 is available in a small-outline package.



FUNCTIONAL BLOCK DIAGRAM





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TERMINAL FUNCTIONS

Table 1.

TERMINAL		DECODINE	00115444710
NAME NO.		DESCRIPTION	SCHEMATIC
AIF OUT	32	IF amplifier output (analog)	Figure 8
AS	17	Address selection input	Figure 1
BS1	14	Band switch 1 output	Figure 2
BS2	13	Band switch 2 output	Figure 2
BS3	12	Band switch 3 output	Figure 2
BS4	1	Band switch 4 output	Figure 2
BUS GND	18	BUS ground	
СР	35	Charge-pump output	Figure 3
DIF OUT1	31	IF amplifier output 1	Figure 9
DIF OUT2	30	IF amplifier output 2	Figure 9
IF GCA CTRL	29	IF GCA CTRL voltage inout	Figure 4
IF GCA GND	25	IF GCA ground	
IF GCA IN1	27	IF GCA input 1	Figure 5
IF GCA IN2	26	IF GCA input 2	Figure 5
IF GCA OUT1	23	IF GCA output 1	Figure 6
IF GCA OUT2	24	IF GCA output 2	Figure 6
IF GND	33	IF ground	
IF IN	9	IF amplifier input	Figure 7
MIXOUT1	8	Mixer output 1	Figure 10
MIXOUT2	7	Mixer output 2	Figure 10
OSC GND	36	Oscillator ground	
P5/ADC	19	Port-5 output/ADC input	Figure 11
RF AGC BUF	11	RF AGC buffer output	Figure 12
RF AGC OUT	10	RF AGC output	Figure 13
RF GND	6	RF ground	1.90.010
SCL	16	Serial clock input	Figure 14
SDA	15	Serial data input/output	Figure 15
UHF OSC B1	40	UHF oscillator base 1	Figure 16
UHF OSC B2	37	UHF oscillator base 2	Figure 16
UHF OSC C1	39	UHF oscillator collector 1	Figure 16
UHF OSC C2	38	UHF oscillator collector 2	Figure 16
UHF RF IN1	2	UHF RF input 1	Figure 17
UHF RF IN2	3	UHF RF input 2	Figure 17
V _{CC}	28	Supply voltage	Tigato 17
VHI OSC B	42	VHF-H oscillator base	Figure 18
VHI OSC C	41	VHF-H oscillator collector	Figure 18
VHI RF IN	4	VHF-H RF input	Figure 19
VLO OSC B	44	VHF-L oscillator base	Figure 20
VLO OSC C	43	VHF-L oscillator collector	Figure 20
VLO RF IN	5	VHF-L RF input	Figure 21
VTU	34	Tuning voltage amplifier output	Figure 3
XTAL1	22		Figure 22
		4-MHz crystal oscillator	
XTAL2	21	4-MHz crystal oscillator	Figure 22
XTALOUT	20	4-MHz crystal oscillator buffer output	Figure 23



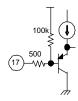


Figure 1. AS

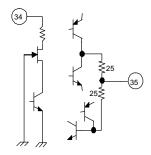


Figure 3. CP and VTU

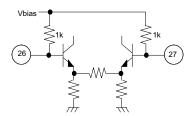


Figure 5. IF GCA IN1 and IF GCA IN2

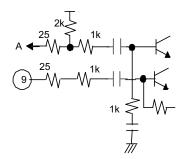


Figure 7. IF IN

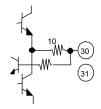


Figure 9. DIF OUT1 and DIF OUT2

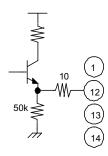


Figure 2. BS1, BS2, BS3, and BS4

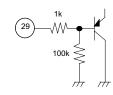


Figure 4. IF GCA CTRL

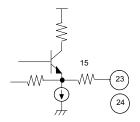


Figure 6. IF GCA OUT1 and IF GCA OUT2

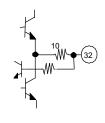


Figure 8. AIF OUT

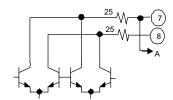


Figure 10. MIXOUT1 and MIXOUT2



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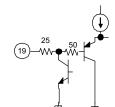


Figure 11. P5/ADC

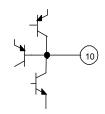


Figure 13. RF AGC OUT

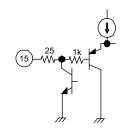


Figure 15. SDA

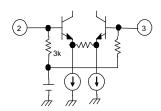


Figure 17. UHF RF IN1 and UHF RF IN2

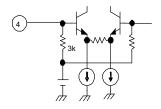


Figure 19. VHI RF IN

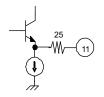


Figure 12. RF AGC BUF

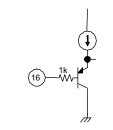


Figure 14. SCL

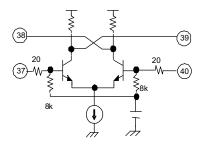


Figure 16. UHF OSC B1, UHF OSC B2, UHF OSC C1, and UHF OSC C2

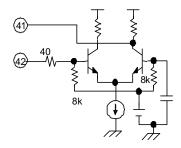


Figure 18. VHI OSC B and VHI OSC C

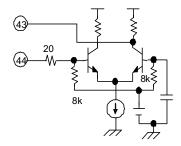


Figure 20. VLO OSC B and VLO OSC C



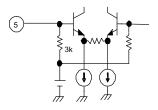


Figure 21. VLO RF IN

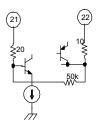


Figure 22. XTAL1 and XTAL2

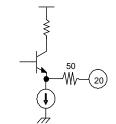


Figure 23. XTALOUT

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ABSOLUTE MAXIMUM RATINGS(1)

over recommended operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range (2)	V _{CC}	-0.4	6.5	V
V_{GND}	Input voltage range 1 (2)	RF GND, OSC GND	-0.4	0.4	V
V _{VTU}	Input voltage range 2 (2)	VTU	-0.4	35	V
V _{IN}	Input voltage range 3 (2)	Other pins	-0.4	6.5	V
P_D	Continuous total dissipation (3)	T _A ≤ 25°C		1438	mW
T _A	Operating free-air temperature range		-20	85	°C
T _{stg}	Storage temperature range		-65	150	°C
T_{J}	Maximum junction temperature			150	°C
t _{SC(max)}	Maximum short-circuit time	Each pin to V _{CC} or to GND		10	s

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Voltage values are with respect to the IF GND of the circuit.

(3) Derating factor is 11.5 mW/°C for T_A ≥ 25°C.

RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	V _{CC}	4.5	5	5.5	V
V_{VTU}	Tuning supply voltage	VTU		30	33	V
I_{BS}	Output current of band switch	BS1 – BS4, one band switch on			10	mA
I_{P5}	Output current of port 5	P5/ADC			- 5	mA
T _A	Operating free-air temperature		-20		85	°C



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric chagnes could cause the device not to meet its published specifications.

IF IN1, MIXOUT1, and MIXOUT2 (pins 7-9) withstand 1.5 kV, and all other pins withstand 2 kV, according to the Human-Body Model (1.5 k Ω , 100 pF).

Product Folder Link(s): SN761644



ELECTRICAL CHARACTERISTICS

Total Device and Serial Interface

 V_{CC} = 4.5 V to 5.5 V, T_{A} = -20°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC} 1	Supply current 1	BS[1:4] = 0100, IFGCA disabled		90	120	mA
I _{CC} 2	Supply current 2	BS[1:4] = 0100, IFGCA enabled		115	145	mA
I _{CC} 3	Supply current 3	BS[1:4] = 0100, IFGCA enabled, I _{BS} = 10 mA		125	155	mA
I _{CC-STBY}	Standby supply current	BS[1:4] = 1100		9		mA
V _{IH}	High-level input voltage (SCL, SDA)		2.3			V
V_{IL}	Low-level input voltage (SCL, SDA)				1.05	V
I _{IH}	High-level input current (SCL, SDA)				10	μΑ
I _{IL}	Low-level input current (SCL, SDA)		-10			μΑ
V _{POR}	Power-on-reset supply voltage (threshold of supply voltage between reset and operation mode)		2.1	2.8	3.5	V
I ² C Interfa	ace				,	
V _{ASH}	Address-select high-input voltage (AS)	V _{CC} = 5 V	4.5		5	V
V _{ASM1}	Address-select mid-input 1 voltage (AS)	V _{CC} = 5 V	2		3	V
V _{ASM2}	Address-select mid-input 2 voltage (AS)	V _{CC} = 5 V	1		1.5	V
V _{ASL}	Address-select low-input voltage (AS)	V _{CC} = 5 V			0.5	V
I _{ASH}	Address-select high-input current (AS)				50	μΑ
I _{ASL}	Address-select low-input current (AS)		-10			μΑ
V _{ADC}	ADC input voltage	See Table 11	0		V_{CC}	V
I _{ADH}	ADC high-level input current	$V_{ADC} = V_{CC}$			10	μΑ
I _{ADL}	ADC low-level input current	V _{ADC} = 0 V	-10			μΑ
V_{OL}	Low-level output voltage (SDA)	$V_{CC} = 5 \text{ V}, I_{OL} = 3 \text{ mA}$			0.4	V
I _{SDAH}	High-level output leakage current (SDA)	V _{SDA} = 5.5 V			10	μΑ
f _{SCL}	Clock frequency (SCL)			100	400	kHz
t _{HD-DAT}	Data hold time	See Figure 24	0		0.9	μs
t _{BUF}	Bus free time		1.3			μs
t _{HD-STA}	Start hold time		0.6			μs
t_{LOW}	SCL-low hold time		1.3			μs
t _{HIGH}	SCL-high hold time		0.6			μs
t _{SU-STA}	Start setup time		0.6			μs
t _{SU-DAT}	Data setup time		0.1			μs
t _r	Rise time (SCL, SDA)				0.3	μs
t _f	Fall time (SCL, SDA)				0.3	μs
t _{SU-STO}	Stop setup time		0.6			μs

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PLL and Band Switch

 V_{CC} = 4.5 V to 5.5 V, T_A = -20°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
N	Divider ratio	15-bit frequency word	512		32767		
f _{XTAL}	Crystal oscillator frequency	$R_{XTAL} = 25 \Omega \text{ to } 300 \Omega$		4		MHz	
Z _{XTAL}	Crystal oscillator input impedance		1.6	2.4		kΩ	
V _{XLO}	XTALOUT output voltage	Load = 10 pF/5.1 k Ω , V _{CC} = 5 V, T _A = 25°C		0.48		Vp-p	
V_{VTUL}	Tuning amplifier low-level output voltage	$R_L = 20 \text{ k}\Omega, \text{ VTU} = 30 \text{ V}$	0.2	0.3	0.46	V	
I_{VTUOFF}	Tuning amplifier leakage current	Tuning amplifier = off, VTU = 30 V			10	μΑ	
I _{CP11}		CP[2:0] = 011		600			
I _{CP10}		CP[2:0] = 010		350			
I _{CP01}	Charge-pump current	CP[2:0] = 001		140		μΑ	
I _{CP00}		CP[2:0] = 000		70			
I _{CP100}		CP[2:0] = 100, Mode = 1		900			
V_{CP}	Charge-pump output voltage	PLL locked		1.95		V	
I _{CPOFF}	Charge-pump leakage current	V _{CP} = 2 V, T _A = 25°C	-15		15	nA	
I _{BS}	Band switch driver output current (BS1-BS4)				10	mA	
V_{BS1}	Band switch driver output voltage (BS1–BS4)	I _{BS} = 10 mA	3			V	
V_{BS2}	Band Switch driver output voltage (BS1-BS4)	$I_{BS} = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$	3.5	3.7		V	
I _{BSOFF}	Band switch driver leakage current (BS1–BS4)	V _{BS} = 0 V			8	μΑ	
I _{P5}	Band switch port sink current (P5/ADC)				- 5	mA	
V_{P5ON}	Band switch port output voltage (P5/ADC)	$I_{P5} = -2 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$			0.6	V	

RF AGC(1)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 44 MHz, IF filter characteristics: f_{peak} = 44 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{OAGC0}	DE ACCOURT autout accuracy comment	ATC = 0		300		nA
I _{OAGC1}	RF AGCOUT output source current	ATC = 1		9		μA
I _{OAGCSINK}	RF AGCOUT peak output sink current	ATC = 0		100		μA
V _{OAGCH}	RFAGCOUT output high voltage (max level)	ATC = 1	3.5	4	4.5	V
V _{OAGCL}	RFAGCOUT output low voltage (min level)	ATC = 1		0.3		V
I _{AGCBUF}	RFAGCBUF output current	ATC = 0		1.5		mA
V _{OAGCBFH}	RFAGCBUF output high voltage (max level)	ATC = 1	3.5	4	4.5	V
V _{OAGCBFL}	RFAGCBUF output low voltage (min level)	ATC = 1		0.3		V
V _{AGCSP00}		ATP[2:0] = 000		114		
V _{AGCSP01}		ATP[2:0] = 001		112		
V _{AGCSP02}		ATP[2:0] = 010		110		
V _{AGCSP03}	Start-point IF output level	ATP[2:0] = 011		108		dΒμV
V _{AGCSP04}		ATP[2:0] = 100		106		
V _{AGCSP05}		ATP[2:0] = 101		104		
V _{AGCSP06}		ATP[2:0] = 110		102		

⁽¹⁾ When AISL=1, RF AGC function is not available at VHF-L band (output level is undefined).



Mixer, Oscillator, IF Amplifier (DIF OUT)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 44 MHz, IF filter characteristics: $f_{peak} = 44 \text{ MHz}$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP	UNIT
G _{C1D}	0 /	f _{in} = 57 MHz ⁽¹⁾	35	in.
G _{C3D}	Conversion gain (mixer-IF amplifier), VHF-LOW	f _{in} = 171 MHz ⁽¹⁾	35	dB
G _{C4D}	0	f _{in} = 177 MHz ⁽¹⁾	35	-ID
G _{C6D}	Conversion gain (mixer-IF amplifier), VHF-HIGH	f _{in} = 467 MHz ⁽¹⁾	35	dB
G _{C7D}	0	f _{in} = 473 MHz ⁽¹⁾	35	.ID
G _{C9D}	Conversion gain (mixer-IF amplifier), UHF	f _{in} = 864 MHz ⁽¹⁾	35	dB
NF _{1D}	Noise figure VIII LOW	f _{in} = 57 MHz	9	dB
NF _{3D}	Noise figure, VHF-LOW	f _{in} = 171 MHz	9	uБ
NF _{4D}	Noise figure, VHF-HIGH	f _{in} = 177 MHz	9	dB
NF _{6D}	Noise ligule, vnr-nigh	f _{in} = 467 MHz	10	uБ
NF _{7D}	Noise figure LIHE	f _{in} = 473 MHz	10	dB
NF _{9D}	Noise figure, UHF	f _{in} = 864 MHz	12	uБ
CM _{1D}	Input voltage causing 1% cross-modulation distortion,	f _{in} = 57 MHz ⁽²⁾	79	dBµV
CM _{3D}	VHF-LOW	f _{in} = 171 MHz ⁽²⁾	79	иБμν
CM _{4D}	Input voltage causing 1% cross-modulation distortion,	$f_{in} = 177 \text{ MHz}^{(2)}$	79	dBµV
CM _{6D}	VHF-HIGH	$f_{in} = 467 \text{ MHz}^{(2)}$	79	иБμν
CM _{7D}	Input voltage causing 1% cross-modulation distortion, UHF	$f_{in} = 473 \text{ MHz}^{(2)}$	77	dΒμV
CM _{9D}	input voltage causing 1% cross-modulation distortion, or in	$f_{in} = 864 \text{ MHz}^{(2)}$	77	αБμν
V_{IFO1D}	IF output voltage, VHF-LOW	f _{in} = 57 MHz	117	dBµV
V_{IFO3D}	ii output voitage, vrii -LOvv	f _{in} = 171 MHz	117	αБμν
V_{IFO4D}	IF output voltage, VHF-HIGH	f _{in} = 177 MHz	117	dΒμV
V_{IFO6D}	ii output voitage, vrii -riigiri	f _{in} = 467 MHz	117	αБμν
V_{IFO7D}	IF output voltage, UHF	f _{in} = 473 MHz	117	dBµV
V_{IFO9D}	ii output voitage, or ii	f _{in} = 864 MHz	117	αБμν
Φ_{PLVL1D}	Phase noise, VHF-LOW	$f_{in} = 57 \text{ MHz}^{(3)}$	-90	dBc/Hz
Φ_{PLVL3D}	THASE HOISE, VIII -LOVV	$f_{in} = 171 \text{ MHz}^{(4)}$	-85	UDC/11Z
Φ_{PLVL4D}	Phase noise, VHF-HIGH	$f_{in} = 177 \text{ MHz}^{(3)}$	-85	dBc/Hz
Φ_{PLVL6D}	T Hase Holse, VIII - HIGH	$f_{in} = 467 \text{ MHz}^{(4)}$	-77	UDC/11Z
Φ_{PLVL7D}	Phase noise, UHF	$f_{in} = 473 \text{ MHz}^{(3)}$	-80	dBc/Hz
Φ_{PLVL9D}	Thase holse, of it	$f_{in} = 864 \text{ MHz}^{(4)}$	-77	UDG/11Z

⁽¹⁾ IF = 44 MHz, RF input level = 70 dB μ V, differential output (2) $f_{undes} = f_{des} \pm 6$ MHz, Pin = 70 dB μ V, AM 1 kHz, 30%, DES/CM = S/I = 46 dB (3) Offset = 1 kHz, CP current = 350 μ A, reference divider = 64

Offset = 1 kHz, CP current = 900 µA, reference divider = 64

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Mixer, Oscillator, IF Amplifier (AIF OUT)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 45.75 MHz, IF filter characteristics: f_{peak} = 44 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP	UNIT
G _{C1A}	0	f _{in} = 55.25 MHz ⁽¹⁾	29	-ID
G _{C3A}	Conversion gain (mixer-IF amplifier), VHF-LOW	f _{in} = 169.25 MHz ⁽¹⁾	29	dB
G _{C4A}	Convenies asia (minor IF amplifies) \(\IIF \)	f _{in} = 175.25 MHz ⁽¹⁾	29	٩D
G _{C6A}	Conversion gain (mixer-IF amplifier), VHF-HIGH	f _{in} = 465.25 MHz ⁽¹⁾	29	dB
G _{C7A}	Convenies asia (minor III amplifies) IIIIII	f _{in} = 471.25 MHz ⁽¹⁾	29	٩D
G _{C9A}	Conversion gain (mixer-IF amplifier), UHF	f _{in} = 862.25 MHz ⁽¹⁾	29	dB
NF _{1A}	Noise figure VIII LOW	f _{in} = 55.25 MHz	9	٩D
NF _{3A}	Noise figure, VHF-LOW	f _{in} = 169.25 MHz	9	dB
NF _{4A}	Noise figure VIII IIICII	f _{in} = 175.25 MHz	9	dB
NF _{6A}	Noise figure, VHF-HIGH	f _{in} = 465.25 MHz	10	uБ
NF _{7A}	Noise figure 1111	f _{in} = 471.25 MHz	10	٩D
NF _{9A}	Noise figure, UHF	f _{in} = 862.25 MHz	12	dB
CM _{1A}	Input voltage causing 1% cross-modulation distortion,	f _{in} = 55.25 MHz ⁽²⁾	79	4D+1/
CM _{3A}	VHF-LOW	f _{in} = 169.25 MHz ⁽²⁾	79	dΒμV
CM _{4A}	Input voltage causing 1% cross-modulation distortion,	f _{in} = 175.25 MHz ⁽²⁾	79	dBµV
CM _{6A}	VHF-HIGH	$f_{in} = 465.25 \text{ MHz}^{(2)}$	79	
CM _{7A}	Input voltage equaing 10/ erace modulation distortion LIHE	f _{in} = 471.25 MHz ⁽²⁾	79	dΒμV
CM _{9A}	Input voltage causing 1% cross-modulation distortion, UHF	$f_{in} = 862.25 \text{ MHz}^{(2)}$	77	αБμν
V_{IFO1A}	IF output voltage, VHF-LOW	f _{in} = 55.25 MHz	117	dBµV
V_{IFO3A}	ir output voltage, viii -LOVV	f _{in} = 169.25 MHz	117	αБμν
V_{IFO4A}	IF output voltage, VHF-HIGH	f _{in} = 175.25 MHz	117	dBuV
V_{IFO6A}	ir output voltage, viii -i liGii	f _{in} = 465.25 MHz	117	αБμν
V_{IFO7A}	F output voltage, UHF	f _{in} = 471.25 MHz	117	dΒμV
V_{IFO9A}	ir output voltage, or ir	f _{in} = 862.25 MHz	117	αБμν
Φ_{PLVL1A}	Phase noise, VHF-LOW	$f_{in} = 55.25 \text{ MHz}^{(3)}$	-95	dBc/Hz
Φ_{PLVL3A}	Filase Hoise, VTF-LOVV	$f_{in} = 169.25 \text{ MHz}^{(3)}$	-95	ubu/nz
Φ _{PLVL4A}	Phase noise, VHF-HIGH	f _{in} = 175.25 MHz ⁽³⁾	-90	dBc/Hz
Φ _{PLVL6A}	Filase Huise, VIIF-IIOI	f _{in} = 465.25 MHz ⁽³⁾	-90	ubt/nz
Φ _{PLVL7A}	Phase noise, UHF	f _{in} = 471.25 MHz ⁽³⁾	-85	dBc/Hz
Φ _{PLVL9A}	Fliase Hoise, UHF	f _{in} = 862.25 MHz ⁽³⁾	-90	ubt/nz

⁽¹⁾ IF = 44 MHz, RF input level = 70 dB μ V (2) $f_{undes} = f_{des} \pm 6$ MHz, Pin = 70 dB μ V, AM 1 kHz, 30%, DES/CM = S/I = 46 dB (3) Offset = 10 kHz, CP current = 70 μ A, reference divider = 128



IF Gain Controlled Amplifier

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 44 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{IFGCA}	Input current (IF GCA CTRL)	V _{IFGCA} = 3 V		30	60	μΑ
V _{IFGCAMAX}	Maximum gain control voltage	Gain maximum	3		V _{CC}	V
V _{IFGCAMIN}	Minimum gain control voltage	Gain minimum	0		0.2	V
G _{IFGCAMAX}	Maximum gain	V _{IFGCA} = 3 V		65		dB
G _{IFGCAMIN}	Minimum gain	V _{IFGCA} = 0 V		-1		dB
GCR _{IFGCA}	Gain control range	V _{IFGCA} = 0 V to 3 V		66		dB
V _{IFGCAOUT}	Output voltage	Single-ended output, V _{IFGCA} = 3 V		2.1		Vp-p
NF _{IFGCA}	Noise figure	V _{IFGCA} = 3 V		11		dB
IM3 _{IFGCA}	Third order intermodulation distortion	f _{IFGCAIN1} = 43 MHz, f _{IFGCAIIN2} = 44 MHz, V _{IFGCAOUT} = -2 dBm, V _{IFGCA} = 3 V		-50		dBc
IIP _{3IFGCA}	Input intercept point	V _{IFGCA} = 0 V		11		dBm
R _{IFGCAIN}	Input resistance (IF GCA IN1, IF GCA IN2)			1		kΩ
R _{IFGCAOUT}	Output resistance (IF GCA OUT1, IF GCA OUT2)			25		Ω

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FUNCTIONAL DESCRIPTION

I²C Bus Mode

I^2C Write Mode (R/ $\overline{W} = 0$)

Table 2. Write Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	MA1	MA0	$R/\overline{W} = 0$	A ⁽¹⁾
Divider byte 1 (DB1)	0	N14	N13	N12	N11	N10	N9	N8	A ⁽¹⁾
Divider byte 2 (DB2)	N7	N6	N5	N4	N3	N2	N1	N0	A ⁽¹⁾
Control byte 1 (CB1)	1	0	ATP2	ATP1	ATP0	RS2	RS1	RS0	A ⁽¹⁾
Band switch byte (BB)	CP1	CP0	AISL	P5	BS4	BS3	BS2	BS1	A ⁽¹⁾
Control byte 2 (CB2)	1	1	ATC	MODE	T3/DISGCA	T2/IFDA	T1/CP2	T0/XLO	A ⁽¹⁾

(1) A: acknowledge

Table 3. Write Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT		
MA[1:0]	Address-set bits (see Table 4)			
N[14:0]	Programmable counter set bits	N14 = N13 = N12 = = N0 = 0		
	$N = N14 \times 2^{14} + N13 \times 2^{13} + + N1 \times 2 + N0$			
ATP[2:0]	RF AGC start-point control bits (see Table 5)	ATP[2:0] = 000		
RS[2:0]	Reference divider ratio-selection bits (see Table 6)	RS[2:0] = 000		
CP[1:0]	Charge-pump current-set bit (see Table 7)	CP[1:0] = 00		
AISL ⁽¹⁾	RF AGC detector input selection bit	AISL = 0		
	AISL = 0: IF amplifier AISL = 1: Mixer output			
P5	Port output/ADC input control bit	P5 = 0		
	P5 = 0: ADC INPUT P5 = 1: Tr = ON			
BS[4:1]	Band switch control bits	BSn = 0		
	BSn = 0: Tr = OFF BSn = 1: Tr = ON			
	Band selection by BS[1:2]			
	BS1 BS2			
	1 0 VHF-LO 0 1 VHF-HI 0 0 UHF 1 Standby mode/stop MOP function (XTALOUT is available in standby mode)			
ATC	RF AGC current-set bit	ATC = 0		
	ATC = 0: Current = 300 nA ATC = 1: Current = 9 μA			
Mode T3/DISGCA T2/IFDA	Mode IFGCA enabled, DIFOUT1, 2 selected = 0: T3/DISGCA, T2/IFDA, T1/CP2, T0/XLO are Test bits and XTALOUT control bit (see Table 8)	MODE = 0 T[3:0] = 0000		
T1/CP2 T0/XLO	Mode T3/DISGCA = 0 : IF GCA enabled = 1 T3/DISGCA = 1 : IF GCA disabled T2/IFDA = 0 : DIFOUT1, 2 selected T2/IFDA = 1 : AIFOUT selected T1/CP2 : Icp control bit, See Table 7 T0/XLO = 0 : XTALOUT enabled T0/XLO = 1 : XTALOUT disabled			

⁽¹⁾ When AISL = 1, RF AGC function is not available at VHF-L band (Output level is undefined.)

Table 4. Address Selection

MA1	MA0	VOLTAGE APPLIED ON AS INPUT
0	0	0 V to 0.1 V _{CC} (Low)
0	1	OPEN, or 0.2 V _{CC} to 0.3 V _{CC} (Mid2)
1	0	0.4 V _{CC} to 0.6 V _{CC} (Mid1)
1	1	0.9 V _{CC} to V _{CC} (High)

Table 5. RF AGC Start Point(1)

ATP2	ATP1	ATP0	IFOUT LEVEL (dBμV)
0	0	0	114
0	0	1	112
0	1	0	110
0	1	1	108
1	0	0	106
1	0	1	104
1	1	0	102
1	1	1	Disabled

(1) When AISL=1, RF AGC function is not available at VHF-L band (output level is undefined).

Table 6. Reference Divider Ratio

RS2	RS1	RS0	REFERENCE DIVIDER RATIO
0	0	0	24
0	0	1	28
0	1	0	32
0	1	1	64
1	0	0	128
1	X	1	80

Table 7. Charge-Pump Current

MODE	CP2	CP1	CP0	CHARGE PUMP CURRENT (μA)
X	0	0	0	70
X	0	0	1	140
X	0	1	0	350
X	0	1	1	600
1	1	0	0	900



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Table 8. Test Bits/XTALOUT Control (1)

MODE	T3/DISGCA	T2/IFDA	T1/CP2	T0/XLO	DEVICE OPERATION	XTALOUT 4-MHz OUTPUT
0	0	0	0	0	Normal operation	Enabled
0	0	0	0	1	Normal operation	Disabled
1	Х	Х	Х	0	Normal operation	Enabled
1	Х	Х	Х	1	Normal operation	Disabled
0	Х	1	Х	Х	Test mode	Not available
0	1	Х	Х	Х	Test mode	Not available

⁽¹⁾ RFAGC and XTALOUT are not available in test mode.

I^2C Read Mode (R/ $\overline{W} = 1$)

Table 9. Read Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	MA1	MA0	$R/\overline{W} = 1$	A ⁽¹⁾
Status byte (SB)	POR	FL	1	1	Х	A2	A1	A0	_

(1) A: acknowledge

Table 10. Read Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA[1:0]	Address-set bits (see Table 4)	
POR	Power-on reset flag	POR = 1
	POR set: power on	
	POR reset: end-of-data transmission procedure	
FL ⁽¹⁾	In-lock flag	
	PLL locked (FL=1), Unlocked (FL=0)	
A[2:0]	Digital data of ADC (see Table 11)	
	Bit P5 must be set to 0.	

⁽¹⁾ Lock detector works by using phase error pulse at the phase detector. Lock flag (FL) is set or reset according to this pulse width disciminator. Hence unstableness of PLL may cause the lock detect circuit to malfunction. In order to stable PLL, it is required to evaluate application circuit in various condition of loop-gain (loo-p filter, CP current), and to verify with whole conditions of actual application.

Table 11. Address Selection⁽¹⁾

A2	A 1	A0	VOLTAGE APPLIED ON ADC INPUT
1	0	0	0.6 V _{CC} to V _{CC}
0	1	1	0.45 V _{CC} to 0.6 V _{CC}
0	1	0	0.3 V _{CC} to 0.45 V _{CC}
0	0	1	0.15 V _{CC} to 0.3 V _{CC}
0	0	0	0 to 0.15 V _{CC}

(1) Accuracy is 0.03 x V_{CC}.



Example I²C Data Write Sequences

Telegram examples:

Start-ADB-DB1-DB2-CB1-BB-CB2-Stop

Start-ADB-DB1-DB2-Stop

Start-ADB-CB1-BB-CB2-Stop

Start-ADB-CB1-BB-Stop

Start-ADB-CB2-Stop

Abbreviations:

ADB: Address byte
BB: Band switch byte
CB1: Control byte 1
CB2: Control byte 2
DB1: Divider byte 1
DB2: Divider byte 2
Start: Start condition
Stop: Stop condition

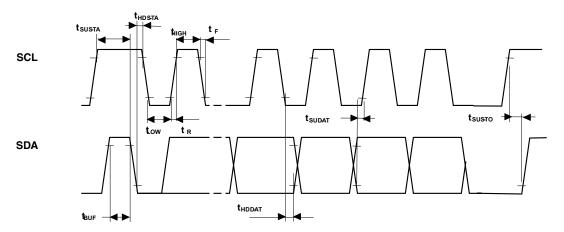


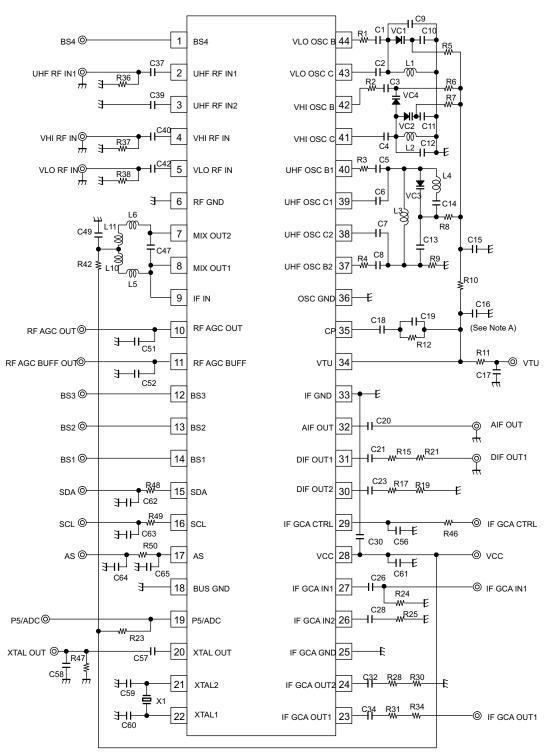
Figure 24. I²C Timing Chart

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APPLICATION INFORMATION



- A. To prevent abnormal oscillation, connect C16, which does not affect a PLL.
- B. This application information is advisory and performance-check is required at actual application circuits. TI assumes no responsibility for the consequences of use of this circuit, such as an infringement of intellectual property rights or other rights, including patents, of third parties.

Figure 25. Reference Measurement Circuit



Table 12. Component Values for Measurement Circuit⁽¹⁾

PARTS NAME	VALUE	PARTS NAME	VALUE
C1 (VLO OSC B)	1 pF	L1 (VLO OSC)	3.0 mm, 7T, wire 0.32 mm
C2 (VLO OSC C)	2 pF	L2 (VHI OSC)	2.0 mm, 3T, wire 0.4 mm
C3 (VHI OSC B)	7 pF	L3 (UHF OSC)	1.8 mm, 3T, wire 0.4 mm
C4 (VHI OSC C)	5 pF	L4 (UHF OSC)	1.8 mm, 3T, wire 0.4 mm
C5 (UHF OSCB1)	1.5 pF	L5 (MIX OUT)	680 nH (LK1608R68K-T)
C6 (UHF OSCC1)	1 pF	L6 (MIX OUT)	680 nH (LK1608R68K-T)
C7 (UHF OSCC2)	1 pF	L10 (MIX OUT)	Short
C8 (UHF OSCB2)	1.5 pF	L11 (MIX OUT)	Short
	OPEN	R1(VLO OSC B)	
C9 (VLO OSC)			0
C10(VLO OSC)	43 pF	R2 (VHI OSC B)	4.7 Ω
C11 (VHI OSC)	51 pF	R3 (UHF OSC B1)	4.7 Ω
C12 (VHI OSC)	0.5 pF	R4 (UHF OSC B2)	0
C13 (UHF OSC)	10 pF	R5 (VLO OSC)	3.3 kΩ
C14 (UHF OSC)	100 pF	R6 (VHI OSC)	3.3 kΩ
C15 (VTU)	2.2 nF/50 V	R7 (VHI OSC)	3.3 kΩ
C16 (CP)	150 pF/50 V	R8 (UHF OSC)	1 kΩ
C17 (VTU)	2.2 nF/50 V	R9 (UHF OSC)	2.2 k
C18(CP)	0.01 u/50 V	R10 (VTU)	3 kΩ
C19(CP)	22 pF/50 V	R11 (VTU)	20 kΩ
C20 (AIF OUT)	2.2 nF	R12 (CP)	47 kΩ
C21 (DIF OUT1)	2.2 nF	R15 (DIF OUT1)	200 Ω
C23 (DIF OUT2)	2.2 nF	R17 (DIF OUT2)	200 Ω
C26 (IF GCA IN1)	2.2 nF	R19 (DIF OUT2)	50 Ω
C28 (IF GCA IN2)	2.2 nF	R21 (DIF OUT1)	0
C30 (VCC)	0.1 uF	R23 (P5/ADC)	Open
C32 (IF GCA OUT1)	2.2 nF	R24 (IF GCA IN1)	(50 Ω)
C34 (IF GCA OUT2)	2.2 nF	R25 (IF GCA IN2)	0
C37 (UHF RF IN1)	2.2 nF	R28 (IF GCA OUT1)	200 Ω
C39 (UHF RFIN2)	2.2 nF	R30 (IF GCA OUT1)	50 Ω
C40 (VHI RF IN)	2.2 nF	R31 (IF GCA OUT2)	200 Ω
C42 (VLO RF IN)	2.2 nF	R34 (IF GCA OUT2)	0
C47 (MIX OUT)	6 pF	R36 (UHF RF IN1)	(50 Ω)
C49 (MIX OUT)	2.2 nF	R37 (VHI RF IN)	(50 Ω)
C51 (RF AGC OUT)	0.15 uF	R38 (VLO RF IN)	(50 Ω)
C52 (RF AGC BUF)	Open	R42 (MIX OUT)	0
C56 (IFGCA CTRL)	0.1 µF	R46 (IFGCA CTRL)	0
C57 (XTAL OUT)	0.01 uF	R47 (XTAL OUT)	5.1 kΩ
C58 (XTAL OUT)	10 pF	R48 (SDA)	330 Ω
C59(XTAL)	27 pF	R49 (SCL)	330 Ω
C60 (XTAL)	27 pF	R50 (AS)	Open
C61 (VCC)	2.2 nF	VC1 (VLO OSC)	MA2S374
C62 (SDA)	Open	VC2 (VHI OSC)	MA2S374
C63 (SCL)	Open	VC3 (UHF OSC)	MA2S372
C64 (AS)	Open	VC4 (VHI OSC)	MA2S372
C65 (AS)	· ·	X1	
000 (AO)	22 pF	^1	4-MHz crystal

⁽¹⁾ IF frequency = 44 MHz Local frequency range : VHF-LOW=101~215 MHz, VHF-HIGH: 221~511 MHz, UHF: 517~908 MHz



APPLICATION INFORMATION (CONTINUED)

Test Circuits

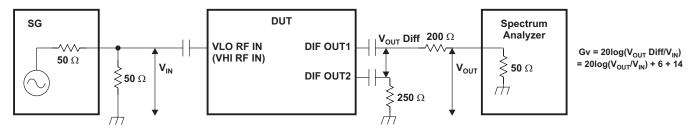


Figure 26. VHF-Conversion Gain-Measurement Circuit (at DIFOUT)

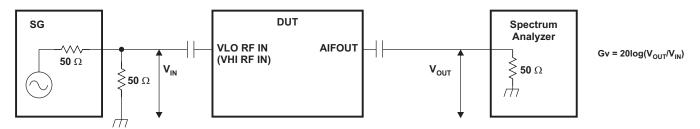


Figure 27. VHF-Conversion Gain Measurement Circuit (at AIFOUT)

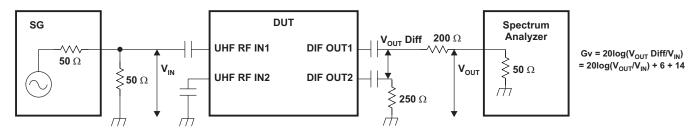


Figure 28. UHF-Conversion Gain-Measurement Circuit (at DIFOUT)

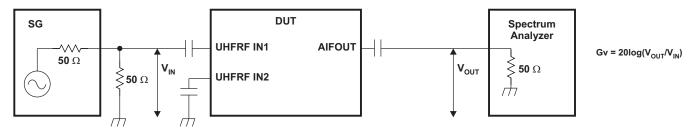


Figure 29. UHF-Conversion Gain Measurement Circuit (at AIFOUT)

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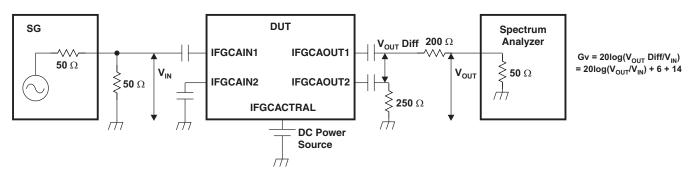


Figure 30. IF GCA Gain Measurement Circuit

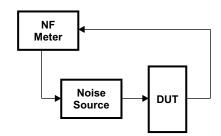


Figure 31. Noise-Figure Measurement Circuit

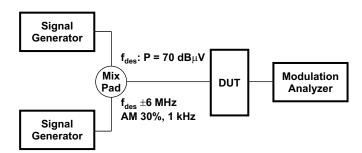


Figure 32. 1% Cross-Modulation Distortion Measurement Circuit



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TYPICAL CHARACTERISTICS

Band Switch Driver Output Voltage (BS1-BS4)

BS OUTPUT CURRENT vs OUTPUT VOLTAGE 5.0 4.5 Band Switch Output Voltage - V V_{CC} = 5.5 V 4.0 V_{CC} = 5.0 V 3.5 V_{CC} = 4.5 V 3.0 2.5 2.0 1.5 1.0 0.5 0.0 2 0 8 4 6 10 12 14 16 18 20 Band Switch Current - mA

Figure 33. Band Switch Driver Output Voltage

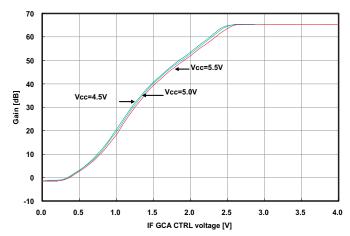


Figure 34. IF GCA Gain vs Control Voltage-1

TYPICAL CHARACTERISTICS (continued)

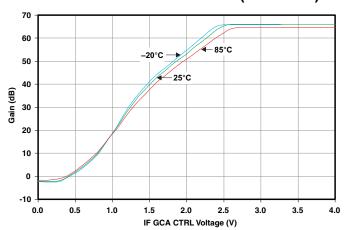


Figure 35. IF GCA Gain vs Control Voltage-2

S-Parameter

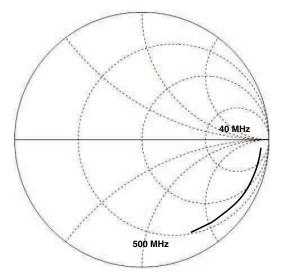


Figure 36. VLO RFIN, VHI RFIN

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TYPICAL CHARACTERISTICS (continued)

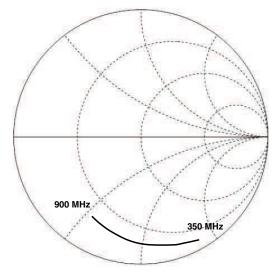


Figure 37. UHF RFIN

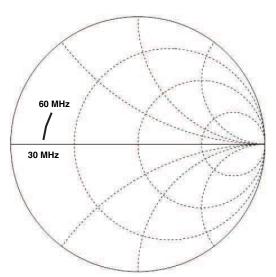


Figure 38. DIFOUT

TYPICAL CHARACTERISTICS (continued)

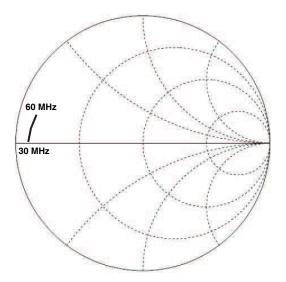


Figure 39. AIFOUT

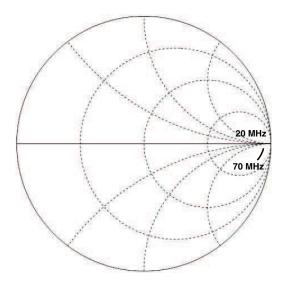


Figure 40. IF GCA IN

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TYPICAL CHARACTERISTICS (continued)

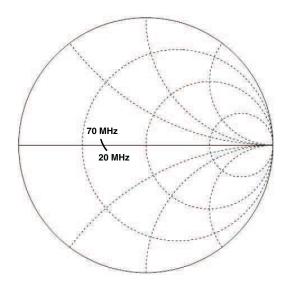


Figure 41. IF GCAOUT



PACKAGE OPTION ADDENDUM

10-Oct-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
SN761644DBTR	OBSOLETE	TSSOP	DBT	44		TBD	Call TI	Call TI	-20 to 85	SN761644	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

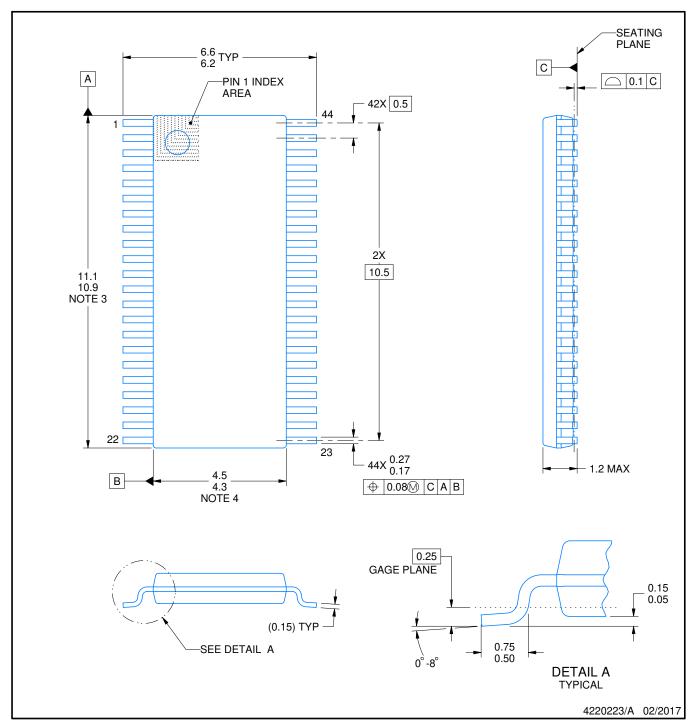
- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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SMALL OUTLINE PACKAGE



NOTES:

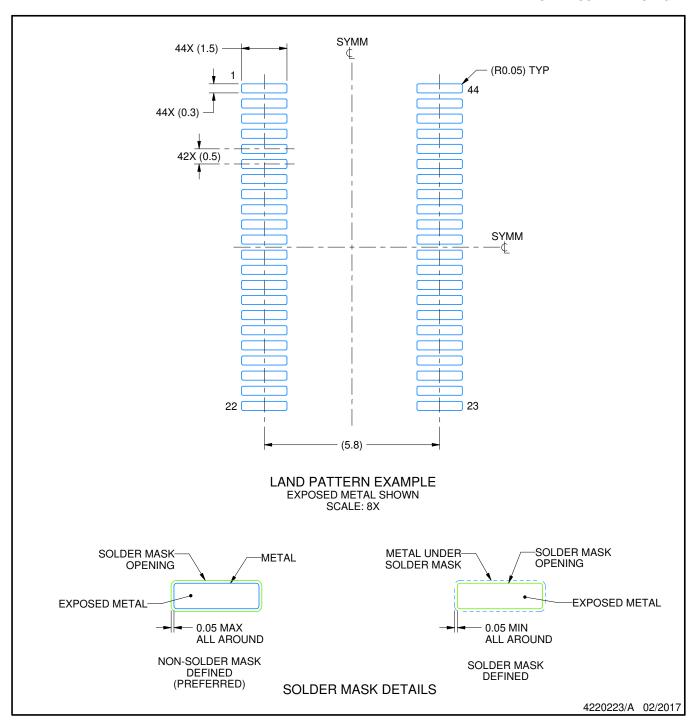
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.



SMALL OUTLINE PACKAGE



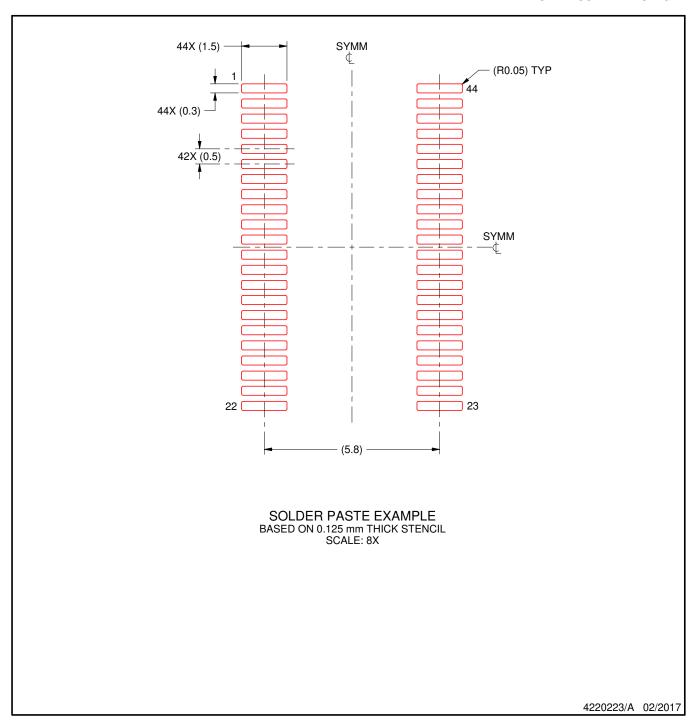
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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